# $B$ allistic transport through coupled $T$-shaped quantum $w$ ires 

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#### Abstract

The ballistic conductance of a coupled $T$-shaped sem iconductor quantum wire (CTQW) are studied. Two types of CTQW are considered, one of wich is a -shaped quantum wire ( Q W ) which consists of two transverse wires on the same side of the $m$ ain $w$ ire and the other a -clone quantum $w$ ire ( CQW ) which consists of two transverse wires on the opposite sides of the $m$ ain $w$ ire. The $m$ ode $m$ atching $m$ ethod and LandauerButtiker theory are em ployed to study the energy dependence of the ballistic conductance. M ost of transm ission pro les of $Q W$ and $C Q W$ are found to be distinguishable for large separation $d$ between the two transverse arm $s$. The transm ission probability m an ifests oscillatory behavior when d is increased. W hen a potential is added to the connection region, it results in decoupling or coupling e ects between the two T-shaped wires according to whether it is positive or negative. W hen magnetic elds are applied to CTQW, the transm ission pro les are found to be a ected profoundly even if the electrons pass through


[^0]the eld free region only.
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## I. IN TRODUCTION

Recently, the $m$ icroetching and epitaxial grow th techniques have enabled sem iconductor nanostructures to be fabricated w ith feature sizes dow $n$ to nanom eters. Such nanostructures include $T$-shaped quantum wires in which quasi-one-dim ensional con nem ent is achieved at the intersection of two quantum wells. B oth experim ental and theoretical studies on the nonlocal ballistic transport of these structures have been stim ulated. In general, T-shaped quantum wires can be fabricated by rst grow ing a $\mathrm{GaA} s / A \mathrm{l}_{\mathrm{x}} \mathrm{Ga}_{1}$ xA sm ultilayers on a (001) substrate, after cleavage, a G aA s quantum well is grown over the exposed (110) surface, resulting in an array of $T$-shaped regions where carrier wavefunctions can be con ned in several tens of angstrom s. T-shaped quantum wires (T Q W ) possess som e im proved optical properties ofone dim ensionalexcitons, such as the excitonic laser em ission, the enhancem ent of excitonic binding energy, and the concentrated oscillator strength. The conductance of such a $m$ esoscopic structure exhibits $m$ any peculiar and interesting features due to its intrinsic nonlocality. $Q$ uantum conductance in $m$ esoscopic structures is the consequence of a com plex scattering process which involves the boundary and the shape of the potential across the structural geom etry as a whole.

Several studies on the electronic transm ission properties for a T-shaped quantum structure have been carried out. ${ }^{1}{ }^{8} \mathrm{M}$ any interesting transm ission characteristics, such as resonant transm ission and resonant re ection in the $T$-shaped structures have been revealed. Such behaviors are caused from the quantum interference which dom inates the ballistic transport regim $e$. Theoretically, one $m$ ay view the resonance as being $m$ ediated by the quasibound states of the system. The system of $T$-shaped quantum wires has open geom etry, therefore, the in jected carriens that travel ballistically over the wire region will across the w ire region and show a strong energy dependent transm ission as a consequence of quantum interference e ect induced by the interplay betw een the propagating $m$ odes of the $w$ ires.

By using the scattering $m$ atrix approach and Landauer-Buttiker theory, Goldoniet. al ${ }^{4}$ have calculated the conductance of $T$-shape and coupled $T$-shaped quantum wires w ith dif-
ferent w ire widths. The transm ission coe cient of the whole coupled $T$-shaped quantum $w$ ires can be obtained easily since the total $T \mathrm{~m}$ atrix is the product of the T m atrioes of the isolated w ires. The double resonance obtained in their result is ascribed to a ngerprint of the bonding and antibonding com binations of the resonance states of the isolated wires. B ohn ${ }^{5}$ has introduced a periodic array of $T$-shaped devices. He show ed that de ected arrays exhibit a unique resonance structure with respect to electrons traveling along the array. The coe cients of the re ection and transm ission through the array can peak sim ultaneously at resonance. Unlike the analogous case in superlattioes, the peaks are at energies where the wavelength satis es the condition $n=2=d$ for som e integer $n$. C onsequently, the scattering wave function possesses nodes at the intersection of the longitudinalarm and the transversal arm, and thus greatly reduces the ux lost to transversal leads. N ikolic and Sordan ${ }^{6}{ }^{7}$ have also studied the transm ission properties of a quantum waveguide system with attached stubs in the ballistic regim e. They found the transconductance and the di erential drain conductance are sm all. Their result suggests lim ited abilities for conventional application of the transistor. Chen et. al. ${ }^{7}$. calculated transm ission of electrons in a T-shaped opened quantum waveguide ( $T O Q W$ ) sub jected to an inhom ogeneous magnetic eld penpendicular to the TOQW plane with mode-m atching technique. The transm ission pro les are found to depend sensitively on geom etric param eters.

In this work, we study a -shaped opened quantum structure and its clone shape, which are four-term inal waveguide-like structures, schem atically as shown in Fig.1. W e take rst the geom etric variation into account. Second, the interconnection region is considered to be acted by a potential. Third, the magnetic eld is considered to apply to the vertical w ires. Unlike the stubs, am s of the structures considered in our case are assum ed to be long enough and open in the longitudinal and the transverse directions. The centers of the tw o vertical arm sare spaced by a distance $d$ as show $n$ in $F$ ig.1. The scattering $m$ atrice are calculated by using $m$ ode-m athing $m$ ethod. O ur $m$ odelw ill be presented brie $y$ in the next section. Results and discussions will be given in the nal section.

## II. M ODELAND FORMALISM

W e m odel the structure geom etry as illustrated in Fig.1: A horizontal w ire w ith a $w$ idth of $W_{1}\left(\mathbb{W}_{2}\right)$ for region $I(V I I)$, a vertical $w$ ire $w$ ith $a \mathrm{width}$ of $W_{2}\left(W_{3}\right)$ for region II (V), an interconnection part for region $\mathbb{I V}$ and a junction region $w$ ith an area of $W_{1} \quad W_{2}$ ( $\mathrm{N}_{1} \quad \mathrm{~W}_{3}$ ) for region III (VI). In thew ire, 2D EG system w ith perfect barrier con nem ent (e.g. high quality interfaces) is assum ed. The individual electron propagates ballistically through the entire w ire. T he transverse potential inside the wire is set to zero. T he Schrodinger equation of individual electron can be w ritten as

$$
\begin{equation*}
\frac{h^{2}}{2 m} r^{2}=E \tag{1}
\end{equation*}
$$

The whole quantum wire can be split into several individual hom ogeneous subregions: horizontal region $I$, vertical regions II and $V$, intersection region III and V I, interconnecting region $\mathbb{I V}$, and the outgoing horizontal region VII. The two intersection regions act as scattering centers. A nd the interconnecting region acts as a connection of the two TQW s. A $n$ nth $m$ ode electron is considered to in ject from left of region I into the $w$ ire. The wave function in region I can be wrilten in term $s$ of a sum of incident and re ecting $m$ odes as

$$
\begin{equation*}
{ }_{n}^{I}(x ; y)={ }_{n}^{I(+)}(y) e^{i k_{n}^{I(+)}\left(x+0: 5 W_{2}\right)}+X_{m}^{X} R_{m n}{ }_{m}^{I()}(y) e^{\left.i k_{m}^{I( }\right)}\left(x+0: 5 W_{2}\right) ; \tag{2}
\end{equation*}
$$

where $\left.k_{n}^{I( }\right)=\frac{q}{k^{2} \quad\left(n_{n}=W_{1}\right)^{2}}$; represents the incident or re ecting $m$ ode, respectively, and $\left.{ }_{n}^{I( }\right)$ are envelope functions in region $I$. The wave functions in regions $I I, V$, and V II are given by a sum of outgoing $m$ odes respectively, ie.,

$$
\begin{align*}
& { }_{n}^{I I}(x ; y)={ }_{m}^{X} S_{m n}^{(1)} \underbrace{I I(+)}_{n}(X) e^{i k_{m}^{I I(+)}}\left(\mathrm{y} 0: 5 W_{1}\right) ; \tag{3}
\end{align*}
$$

where represents the upw ard or dow nw ard arm and

The wave function in region $\mathbb{I V}$ is given by the sum of rightgoing (+) and leftgoing ( ) m odes,

In region III and region $V$ I, allm odes $m$ ust be taken into account, thus

$$
\begin{align*}
& { }_{n}^{V I}\left(x^{0} ; y\right)={ }_{j}^{x} f_{j}(y){ }_{x}^{h} d_{j n} \sin k_{j}^{0}\left(x^{0} 0: 5 W_{3}\right)+e_{j n} \sin k_{j}^{0}\left(x^{0}+0: 5 W_{3}\right){ }^{i} \\
& +{ }_{j}^{x} g_{j}^{0}\left(x^{0}\right) h_{j n} \sin k_{j}^{\infty}\left(\begin{array}{l}
y \\
0: 5 W \\
1
\end{array}\right) \quad: \tag{8}
\end{align*}
$$

Here $f_{j}(y)={ }^{q} \frac{\overline{2}}{\frac{2}{W_{1}}} \sin \frac{j}{W_{1}}\left(y+0: 5 W_{1}\right) ; g_{j}(x)=\frac{q}{\frac{2}{W_{2}}} \sin \frac{j}{W_{2}}\left(x+0: 5 W_{2}\right) \quad$ and $g_{j}^{0}\left(x^{0}\right)=$ ${ }^{q} \frac{2}{W_{3}} \sin \frac{j}{W_{3}}\left(x^{0}+0: 5 W_{3}\right)$ represent the transverse wave functions of the electron in $m$ ode $j$ inside the di erent regions of the $w$ ires, and are used as the expansion bases. The wave num bers $k_{j}^{0}=\frac{q}{k^{2} \quad\left(j=W_{1}\right)^{2}} ; k_{j}^{\infty}={ }^{q} \overline{k^{2} \quad\left(j=W_{2}\right)^{2}}$; and $k_{j}^{\infty}=^{q} \overline{k^{2} \quad\left(j=W_{3}\right)^{2}}$ are either real for propagating $m$ odes or pure im aginary for evanescent $m$ odes. $N$ ow expand the wavefunctions in tem s of a set of com plete bases corresponding to the transverse eigenfunctions in regions I, II, IV , V and V II, respectively as

$$
\begin{align*}
& { }_{m}^{I V}()(y)={ }_{j}^{X}{ }_{j m}^{I V()} f_{j}(y) ; \tag{11}
\end{align*}
$$

and

$$
\begin{equation*}
{ }_{n}^{\mathrm{VII}(+)}(y)={ }_{j n}^{\mathrm{VII}(t)} f_{j}(y): \tag{13}
\end{equation*}
$$

Substituting these functions into Eq.(1) for a given Ferm i energy $E_{F}$, we obtain ve sets
 functions $f{ }_{n}^{I()}(y) g, f{ }_{n}^{I I(+)}(y) g, f{ }_{n}^{I V}()(y) g, f{ }_{n}^{V}()(y) g$, and $f{ }_{n}^{V I I(t)}(x) g$. By using boundary $m$ atching technique, ${ }^{9}$ we can derive all coe cients in Eqs . (2) $\left\{\right.$ (8) such as $\mathrm{fr}_{\mathrm{m}} \mathrm{n}$, $f f_{m}(1) ~ g, f s_{m}^{(2)} g, f u_{m} g, f v_{m} g, f t_{n n} g, f a_{j n} g, f b_{j n} g, f C_{j n} g . f d_{j n} g, f e_{j n} g$, and $f h_{j n} g$.

The group velocities of the $j$ th state in region $I$, II, V and V II are respectively
as well as

$$
\begin{equation*}
V_{j}^{V I I(+)}=\frac{h^{Z}}{\mathrm{Z}_{0}} \underset{0: 5 \mathrm{~W}_{1}}{0: 5 \mathrm{~W}_{1}}{\underset{j}{\mathrm{VII}(+)}}_{\mathrm{V}}^{\mathrm{V}) \mathrm{k}_{\mathrm{j}}^{\mathrm{VII}(+)}} \underset{\mathrm{j}}{\mathrm{VI(t)}}(\mathrm{y}) \mathrm{dy}: \tag{17}
\end{equation*}
$$

The transm ission probabilities $E_{n j}$ (in region VII) and $\boldsymbol{s}_{n j}^{(1)} s_{n j}^{(2)} \quad$ (in region II and region $V$ ) from the incident $m$ ode $n$ to the nalm ode $j$, and the re ection probability $w_{n j}$ from the incident $m$ ode $n$ to the nalm ode $j$ (in region I) can be obtained, respectively, as follow $s$ :

$$
\begin{gather*}
\Phi_{n j}=\frac{V_{j}^{I()}}{V_{n}^{I(+)}} j r_{n j} f ;  \tag{18}\\
s_{n j}^{(1)}=\frac{V_{j}^{I I I(+)}}{V_{n}^{I(+)}} j s_{n j}^{(1)} f ;  \tag{19}\\
s_{n j}^{(2)}=\frac{V_{j}^{I I I(+)}}{V_{n}^{I(+)}} j s_{n j}^{(2)} f^{f ;}  \tag{20}\\
\epsilon_{n j}=\frac{V_{j}^{I I(+)}}{V_{n}^{I(+)}} j t_{n j} \rho ; \tag{2}
\end{gather*}
$$

It should be em phasized that the expansions (9) \{ (13) involve an in nite sum including all possible evanescent $m$ odes. In practioe, in order to solve this set of equations num erically, we have to truncate the sum at som e nite num ber which should be large enough to achieve a desired accuracy. The num erical convergence can be checked by ux conservation. The relationship ${ }^{P}{ }_{j}\left(\ell_{j n}+\Psi_{j n}+s_{j n}\right)=1$ should be ful led accurately.

The total transm ission coe cients $T$ and $S$ are then given by

$$
\begin{align*}
& T=\sum_{n=1 j=1}^{X_{1} \mathbb{X}_{2}} E_{n j} ;  \tag{22}\\
& S=\sum_{n=1 j=1}^{X_{1} X_{3}^{3}} S_{n j}: \tag{23}
\end{align*}
$$

$W$ here $\mathrm{N}_{1}, \mathrm{~N}_{2}$ and $\mathrm{N}_{3}$ are the numbers of propagating modes in regions I , II and III , respectively. The conductance $G$ at zero tem perature is given by the Landauer\{Buttiker formula:

$$
\begin{equation*}
G_{t}=\left(2 e^{2}=h\right) T \tag{24}
\end{equation*}
$$

and

$$
\begin{equation*}
G_{s}=\left(2 e^{2}=h\right) S: \tag{25}
\end{equation*}
$$

W e also evaluate the probability density of electrons in the quantum wire by adding the contributions from all propagating $m$ odes as

$$
\begin{equation*}
(x ; y)=x_{n=1}^{x^{N}} j n_{n}(x ; y) \mathcal{J}^{2}=k_{n}: \tag{26}
\end{equation*}
$$

III. NUMERICALRESULTSAND D ISCUSSIONS
A. Transm ission P roperties w ith $G$ eom etric $V$ ariations

Figs. 1 (a) and (b) schem atically depict the geom etry of the \{shaped QW (QW) and the -clone QW ( CQW ).W e present our results in term s of som e convenient param eters:

1) the rst threshold energy $E_{1}=\frac{h^{2}}{2 m}\left(=W_{1}\right)^{2}$ through horizontal $w$ ire, 2) the distance $d$ betw een tw o center of the intersections of vertical wires and horizontalw ire, 3) the ratios of w idths $=\mathrm{W}_{2}=\mathrm{W}_{1}$ and $=\mathrm{W}_{3}=\mathrm{W}_{2}$.

First of all, we consider that all w ires are the sam e width, nam ely W . Transm ission probabilities are calculated with varying $\mathrm{k}_{\mathrm{F}}$ as show in F ig. 2 (a) and (b) for di erent d . C urves from bottom to top in Fig 2 (a) are shifted by 1.0 for clarity and correspond to the cases of $d=1,1.1,12,1.3,1.5,1.7$, and $2.0 \mathrm{~W}_{1}$, respectively. A nd curves from bottom to top in Fig 2 (b) are shifted by 1.0 for clarity and correspond to the cases of $d=2,2.5,3.0$, and $5.0 \mathrm{~W}_{1}$, respectively. H ereafter, we present the transm ission probabilities of the $\mathrm{Q} W$ system as solid lines and those of the CQW system as the dotted lines in all gures.

For $d=1$, the vertical $w$ ires are adjacent to each other. Thus, a $Q W$ with $d=1$, can be regarded as a TQW with a double width in the vertical arm except there is an in nite thin wall along the vertical arm axis. H owever, one can note from the gure that the pro les of transm ission of a $Q W$ w th $d=1$ are quite di erent from the transm ission pro les of $\operatorname{TQW}$ w th the samewidth ( $2: \mathrm{OW}_{1}$ ) of the vertical am ${ }^{8}$. In fact, the bottom curve of $Q W \quad(d=1)$ is sim ilar to the result obtained in $T Q W$ with a vertical arm of 1:OW ${ }_{1}$ w idth as obtained in $R$ ef (8). This im plies that the two system s are sim ilar exoept the transm ission amplitude is suppressed in a QW system. For the CQW, the sharp dip at $\mathrm{k}_{\mathrm{F}}=2: 0=\mathrm{W}_{1}$ is replaced by a wider valley before $\mathrm{k}_{\mathrm{F}}=2: 0 \quad=\mathrm{W}_{1}$. The transm ission behaviors of the two structures ( QW and CQW ) are di erent in general, how ever, their periodic oscillations are the sam e. T he period of the oscillation is dom inated by the distance d as can be seen from Fig 2. The periodicity can be tted as $n_{1}=2 d$ approxim ately, where n is the num ber of periods in one m ode, and ${ }_{\mathrm{I}}=2=\left(\mathrm{k}_{\mathrm{F}} \quad=\mathrm{W}{ }_{1}\right)$ denotes the longitudinal wave length of the incident electron waves. Thus, once one nds two peaks in the region 1:0 $<\mathrm{k}_{\mathrm{F}} \mathrm{W}_{1}=<2: 0$ for $\mathrm{d}=1 \mathrm{~W}_{1}$, then four peaks w ill be found for $\mathrm{d}=2 \mathrm{~W}_{1}$, and so on. Curves in both structures ( QW and CQW ) possess peak-dip structures. Especially, these peak-dip structures are $m$ ore clear for larger $d$ at $k_{F}=2: 0=W{ }_{1}$. On the contrary,
they are observed only in certain circum stance for sm aller d. A coording to the previous result ${ }^{8}$, there exists a localized state in the intersection region for a symm etric TOQW w ith sam e wavenum ber $\mathrm{k}_{\mathrm{F}}=2: 0=\mathrm{W}_{1}$. The peak-dip structure at $\mathrm{k}_{\mathrm{F}}=2: 0=\mathrm{W}_{1}$ can be ascribed to this localized state. The peak-dip structure is found at $k_{F}=2: 0 \quad=W_{1}$ on the curve $w$ ith $d=1: 5$ for $C Q W$. Ford larger than $1: 5 \mathrm{~W}_{1}$, the peak-dip structure is sharper in $C Q W$ than that in $Q W$.

D ue to the fact that both $Q W$ and $C Q W$ structures are equivalent to a system of tw O TQW S, onem ay expect that the transm ission properties of these tw o structures w ill be the sam e if the coupling between the constituent TQW s becom es very weak. H ow ever, our result does not $m$ anifest this accordance. On the contrary, the two transm ission pro les are still distinguishable from each other even for large d. It is also found that the transm ission probabilities vary periodically $w$ ith $d$ for a xed wavenumber as shown in $F$ ig.3. These behaviors are the essential characteristics of ballistic theory.

N ow let us consider the case that the widths of the vertical w ires are the sam e, while the ratio of the width of the vertical wire to the horizontal wire is varied. The result is displayed in Fig. 4. For sim plicity, we de ne the ratio of the $w$ idth of the vertical wire to the horizontal wire as $=\mathrm{W}_{2}=\mathrm{W}_{1}=\mathrm{W}_{3}=\mathrm{W}_{1}$. A nd the distance d is set to $2 \mathrm{~W}_{1}$. Curves from the bottom to the top are shifted by 1.0 individually for clarity and correspond to the cases of $=0.1,0.2,0.3,0.5,0.7,1.0,1.5,2.0$ and 4.0 , respectively, as show $n$ in the gure. For extrem ely sm all, perfect stepw ise pro les are observed in both structures. The transm issions are strongly suppressed when the ratio is large (e.g. 2.0 and 4.0). The solid curve for $=0: 5$ agrees w ith the result of previous work ${ }^{4}$. A double resonance is evident either on the curve of $=0: 3$ or the curve of $=0: 5$. They are the signature of the bonding and antibonding com binations of the resonant quasi-1D state of isolated wires.

Finally, the transm ission pro les in the QW and CQW w ith verticalw ires of di erent w idth are considered. For sim plicity, the w idth of one verticalw ire is kept to be the sam e as that of the horizontal $w$ ire. The calculated transm ission pro les for $W_{1}=W_{3}$ and di erent $\mathrm{W}_{2}$ are show n in F ig. 5 (a) and those for $\mathrm{W}_{1}=\mathrm{W}_{2}$ and various $\mathrm{W}_{3}$ are show in F ig. 5 (b).

C urves are o set for clarity. C urves from bottom to top correspond to the cases of $=0.1$, $0.2,0.3,0.5,0.7,1.0,2.0,4.0$, and 5.0 , respectively. W here is the ratio of the w ire w idth of the vertical w ire to the horizontal w ire. It is observed that the transm ission probability is drastically suppressed for large as can be seen from the upper curves in (a) and (b). C om paring curves in (a) and (b), we observe that the transm ission pro les are the sam e. W hen issmall, the transm ission pro les of the QW and CQW becom e indistinguishable and alm ost the sam e as that of $\mathrm{T} Q \mathrm{~W}$ system. The double resonance can be observed again.

## B. Transm ission U nder an A dditional Potential

We now consider the case that an additional scalar potential is applied to the interconnection region IV.T he applied potential can be negative or positive for attracting or depleting electrons. The di erent coupling pro les are interesting and $m$ ay be im portant for practical usage of the $m$ esoscopic devioes.

Fig. 6 presents the calculated transm ission pro les for di erent potential strength $V_{4}$ in unit of $E_{1}$. H ere we consider $W_{3}=W_{2}=W_{1}$, and $d=2 W_{1} \cdot F$ igs. 6 (a) and (c) correspond to the positive potential for electrons. Figs. 6 (b) and (d) correspond to negative potential. C urves are o set for clarity. A s show n in F ig. 6 (a), one can observe that the positive potential does not a ect the transm ission very much when $V_{4} \quad E_{1}$. >From $F$ igs. 6 (a) and (c), two features are show $n$ : (1) the onset is shifted due to the depletion potential; (2) the positions of transm ission dips are not changed. On the contrary, Figs.6(b) and (d) show that the additional negative potential a ects the transm ission $m$ uch stronger than the positive one. Especially, the potential enhances the coupling between the two TOQW s as one can note from the fact that the resonant dip-peak-dip structure becom es broader and shallow er when the potential is increased. $M$ ore peaks are on the curves and the positions of dips are not changed as the case of positive potential. M oreover, it can be observed that discrepancy between the two structures becom es prom inent as the potential strength is increased. T hese results $m$ anifest that the negative potential increases the coupling strength betw een the two
individual TOQW s.
C. Transm issions under the in uence of surrounding magnetic $F$ ields

Finally, m agnetic elds are considered to apply to the vertical w ires only, therefore, the electrons pass through the $m$ ain arm regions with no additional eld. W e shall study the e ect of the surrounding $m$ agnetic elds on the transm ission behavior. First, we consider the $m$ agnetic eld is applied only to one of the vertical wires, i.e on arm II or arm V.T he direction of the eld is perpendicular to the 2D EG plane. Transm ission probabilities are calculated as a function of Ferm iwave vector as depicted in $F$ ig.7. Curves in $F$ ig. 7 (a) are o set for clarity, and correspond to the cases ofm agnetic eld strength $B=-1.0,-0.7,-0.5$, $-0.3,-02,-0.1,0.1,02,0.3,0.5,0.7,1.0$ Tesla, respectively in region $I I . T$ hose show $n$ in Fig. 7 (b) are the sam e except the $m$ agnetic eld is applied to region V . $>$ From these curves, one can conclude that: (1) the magnetic eld does a ect the transm ission, although the electrons do not pass through the region w ith $m$ agnetic eld directly. This phenom enon is according w th A haronov-B ohm e ect. H ow ever, no periodic behavior can be found. (2) For the QW system as shown in solid curves in $F$ igs. 7 (a) and (b), both cases show a one-to-one correspondence to each other. This $m$ anifests that the in uence of the magnetic eld on the transm ission pro le depends only on the $m$ agnetic eld strength. H ow ever, there is no correspondence in the case of $C Q W$ which is presented by the dotted lines in $F$ igs. 7 (a) and (b). (3) G enerally speaking, opposite polarity of the m agnetic eld causes di erent in uence on the transm ission in CQW system s.

The transm ission pro les versus Ferm iwave num ber $k_{F}$ for the case that the $m$ agnetic eld being applied to both regions II and $V$, are displayed in $F$ ig. 8 . $F$ ig. 8 (a) presents the transm ission in the QW s and CQW s w ith same polarity in both vertical arm $s$, and Fig. 8 (b) presents those w ith opposite polarity to each other in the two vertical arm s. The curves are o set for clarity. T he solid lines represent the QW system $s$ and dotted lines represent the $C Q W$ s system $s$. It is found that for the case of $Q W s$, though the geom etry
and the applied eld are sym $m$ etric, the transm ission probabilities are di erent from each other (e.g. the solid curves w ith $v=0: 2$ and $0: 2$ ) as can be seen from $F$ ig. 8 (a) . H ow ever, for the case of $C Q W s$, the transm ission are polarity independent as can be noted from the dotted curves in Fig. 8 (a). No such symm etry can be found in CQW as shown in $F$ ig. 8 (b). Furtherm ore, peak-dip structures are evident both in $F$ igs.(a) and (b) at high eld situations, though the electrons alw ays $m$ ove in eld free region. O ne can expect that the transm ission pro les will becom e stepw ise structures when the applied magnetic eld is extrem ely high. A nd in the interm ediate eld strength, the $m$ agnetic eld changes the oscillatory behavior of the pro les signi cantly.

## IV.SUM M ARY

In the present work, the transm ission properties of the coupled TOQW s are found to be very sensitive to the geom etric con gurations as well as the strength and polarity of the applied elds. A double resonance is observed on the pro les at certain ratio of the width of the verticalw ire to the horizontal w ire. The transm ission is suppressed drastically as the width of one or both vertical wires becom e large. M ost of the transm ission pro les of QW and $C Q W$ are distinguishable even for large inter- distance $d$ between the two vertical w ires. The transm ission pro les exhibit oscillatory behavior as the distance $d$ is increased and $m$ anifest periodic features as the distance $d$ is varied. $T$-shaped quantum $w$ ires have been proposed to achieve the quantum interference e ect by controlling the length of its lateral closed arm s. In the present study, it is found that the interference pattem can be easier to obtain by m odulating the length and width of transversal arm $s$ and the distance betw een arm s.

W hen a potential is added to the connection region, it results in decoupling or coupling e ects betw een the tw OTQW s according to whether it is positive or negative. This behavior is observed by the altemating occurrence ofthe successive dips and valleys w hen the potential is increased positively.

Though the electrons pass through only the eld free region, the magnetic eld still a ects the transm ission in the QW s profoundly. The perfect transm ission can be seen only in the high $m$ agnetic eld region.

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## FIG URES

F IG.1. (a) The schem atic illustrations of the geom etries of $a$ Q W system. (b) a CQW system .

FIG.2. Thetransm ission $T$ versus $K_{F}$ fordi erent $d w h i c h$ is converted to $v$ by $d=(1+v) W_{1}$. A $l l$ w ires have sam e width. (a) $d \quad 2 \mathrm{~W}_{1}$ (b) $\mathrm{d} 2 \mathrm{~W}_{1}$. $T$ he solid lines represent the $T$ of $Q W$, while the dotted lines represent the $T$ of $C Q W$.

F IG . 3. The periodic behaviors of transm issions versus dfor $W_{3}=W_{2}=W W_{1}: T_{1}\left(T_{2}\right) ; S_{1}\left(S_{2}\right)$ represent the total transm ission coe cients $T$ and $S$ as de ned in Eqs.(22) and (23) for $Q W$ ( CQW).

FIG.4. Transm ission versus $k_{F}$ for di erent. W here is the ratio of the $w$ idth of the vertical arm to the horizontal arm. A nd $d=2 \mathrm{~W}_{1}$. The solid lines represent the $T$ of $Q \mathrm{~W}$, while the dotted lines represent the $T$ of $C Q W$. Curves are o set for clarity.

F IG . 5. Sam e as Fig 2, except the w idth of one vertical arm varies. (a) The width of 2 varies, (b) the w idth ofW 3 varies. $T$ he solid lines represent the $T$ of $Q W$, while the dotted lines represent the $T$ of $C Q W$.

F IG . 6. Transm ission pro les versus $k$ for a potential $V_{4}$ applied to the region $\mathbb{I V}$. (a) and (c) correspond to the positive potential and (b) and (d) correspond to the negative potential. T he solid lines represent the $T$ of $Q W$, while the dotted lines represent the $T$ of $C Q W$.

FIG.7. Transm ission pro les versus for the magnetic eld applied to only one vertical arm. (a) to region $I I$, and (b) to region $V$. The solid lines represent the $T$ of $Q W$,w hile the dotted lines represent the $T$ of $C Q W$. Curves are o set for clarity.

FIG. 8. Transm ission pro les versus $k$ for the $m$ agnetic eld applied to both vertical arm $s$. (a) sam e polarity, and (b) opposite polarity in II and V.The solid lines represent the $T$ of Q W , while the dotted lines represent the $T$ of $C Q W . C$ urves are o set for clarity.




(a)




(d)







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